

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,273,647 B2
APPLICATION NO. : 10/809712
DATED : September 25, 2007
INVENTOR(S) : Nishikawa et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, item [56] Under References Cited, Non-Patent Publication should be included: K. Nakai; "NITROGEN AND CARBON EFFECT ON THE FORMULATION OF GROWN-IN DEFECTS AND OXYGEN PRECIPITATION BEHAVIOR"; the 52nd Conference of the Japanese Association for Crystal Growth, Bulk Growth Section Meeting; February 8, 2000, pgs. 6-9

Column 15, line 17:

"the annealing process is performed at 11000°C - 1250°C for"
should read:

--the annealing process is performed at 1100°C - 1250°C for--

Column 16, line 8:

"oxygen precipitates formed at a density of 1×10^{14} counts/"
should read:

--oxygen precipitates formed at a density of 1×10^4 counts/--

Signed and Sealed this

Seventeenth Day of June, 2008



JON W. DUDAS
Director of the United States Patent and Trademark Office